



General Description

The WST6006 is the highest performance trench N-CH MOSFET with extreme high cell density , which provide excellent R_{DSON} and gate charge for most of the small power switching and load switch applications.

The WST6006 meet the RoHS and Green Product requirement with full function reliability approved.

Features

- High-speed switching
- Green Device Available
- ESD Protected:2KV

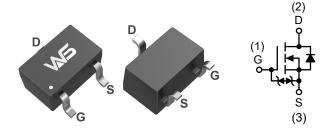
Product Summery

BV _{DSS}	R _{DSON}	I _D
60V	1400mΩ	0.115A

Applications

- High Frequency Point-of-Load Synchronous Buck Converter for MB/NB/UMPC
- Networking DC-DC Power System
- Load Switch

SOT-323-3L Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	60	V
V_{GS}	Gate-Source Voltage	±20	V
I _D @T _A =25℃	Continuous Drain Current, V _{GS} @ 10V ¹	0.115	Α
I _D @T _A =70°C	Continuous Drain Current, V _{GS} @ 10V ¹	0.075	А
I _{DM}	Pulsed Drain Current ²	1.0	А
P _D @T _A =25°C	Total Power Dissipation ³	0.2	W
T _{STG}	Storage Temperature Range	-55 to 150	$^{\circ}$
TJ	Operating Junction Temperature Range	-55 to 150	$^{\circ}$

Thermal Data

Symbol	Parameter	Тур.	Max.	Unit
$R_{ heta JA}$	Thermal Resistance Junction-Ambient ¹		625	°C/W



Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Parameter Conditions		Тур.	Max.	Unit	
BV _{DSS}	Drain-Source Breakdown Voltage	Breakdown Voltage V _{GS} =0V , I _D =250uA				V	
$\triangle BV_{DSS}/\triangle T_{J}$	BV _{DSS} Temperature Coefficient	Reference to 25℃, I _D =1mA		0.05		V/°C	
В	Static Drain-Source On-Resistance ²	V _{GS} =10V , I _D =0.5A		1400	2200	mΩ	
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =4.5V , I _D =0.05A		1800	2500		
V _{GS(th)}	Gate Threshold Voltage	\/ -\/ -250\	1	1.6	2.5	V	
$\triangle V_{GS(th)}$	V _{GS(th)} Temperature Coefficient	$-V_{GS}=V_{DS}$, $I_D=250uA$		-3.7		mV/℃	
	V _{DS} =60V , V _{GS} =0V , T _J =25℃				1		
I _{DSS}	Drain-Source Leakage Current	V_{DS} =60V , V_{GS} =0V , T_{J} =55 $^{\circ}$ C			5	uA uA	
I _{GSS}	Gate-Source Leakage Current	V_{GS} = $\pm 20 V$, V_{DS} = $0 V$			±10	uA	
gfs	Forward Transconductance	V _{DS} ≥ 2.0 V DS(on), ID = 200 mA)		80		mS	
T _{d(on)}	Turn-On Delay Time			1.8	3.3		
Tr	Rise Time	$V_{DD}=25V,I_{D}=500\text{mA},R_{G}=25\Omega,$		7	6		
$T_{d(off)}$	Turn-Off Delay Time	$RL = 50\Omega, Vgs=10V$		6.8	13.6	ns	
T _f	Fall Time			11	40	1	
Ciss	Input Capacitance			17	50		
C _{oss}	Output Capacitance	V_{DS} =25V, V_{GS} = 0V, f=1MHz		10	25	pF	
C _{rss}	Reverse Transfer Capacitance			2.5	5.0		

Diode Characteristics

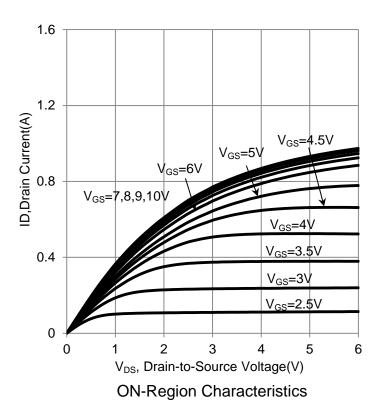
Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
I _S	Continuous Source Current ^{1,4}	// =// =0\/ Force Current			0.115	Α
I _{SM}	Pulsed Source Current ^{2,4}	V _G =V _D =0V , Force Current			0.8	Α
V_{SD}	Diode Forward Voltage ²	I _S =115mA, V _{GS} =0V			1.5	V

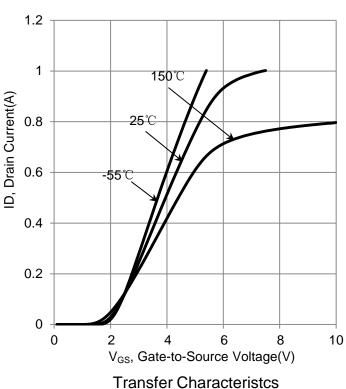
Note:

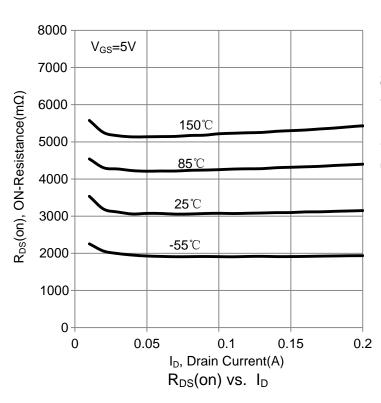
- 1. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width \leq 300us , duty cycle \leq 2%
- 4. The data is theoretically the same as I_D and I_{DM} , in real applications, should be limited by total power dissipation.

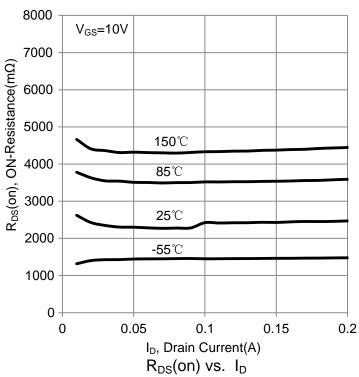


Typical Characteristics





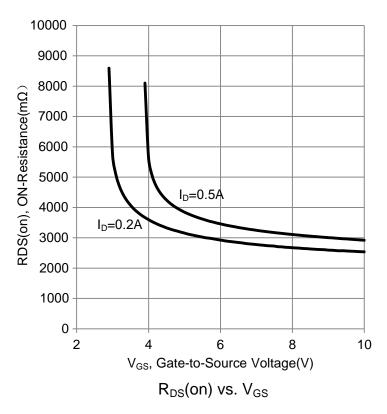


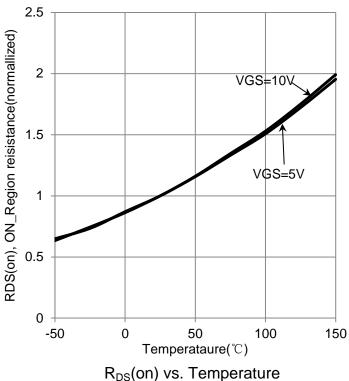


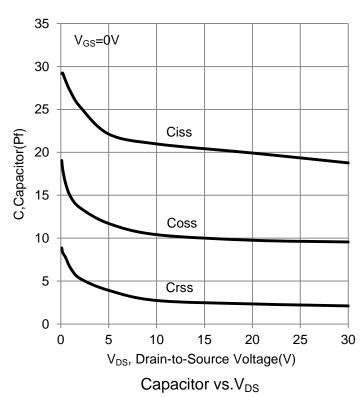


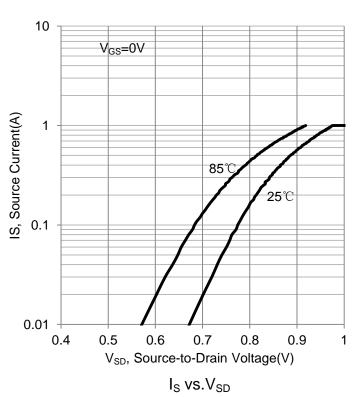


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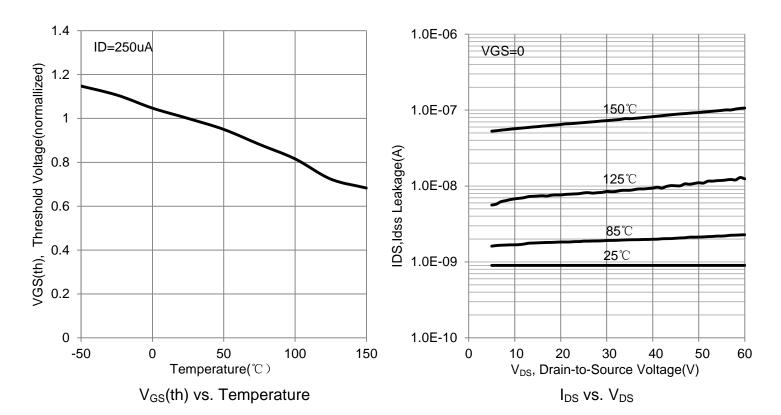






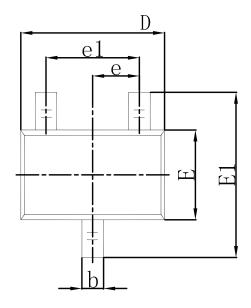


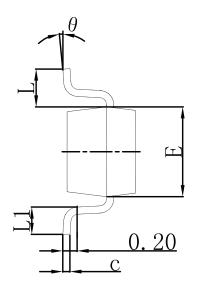
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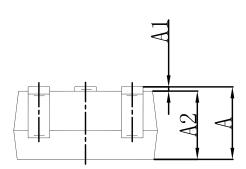




Packaging information







Symbol	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min	Max	Min	Max	
Α	0.900	1.100	0.035	0.043	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.000	0.035	0.039	
b	0.200	0.400	0.008	0.016	
С	0.080	0.150	0.003	0.006	
D	2.000	2.200	0.079	0.087	
E	1.150	1.350	0.045	0.053	
E1	2.150	2.450	0.085	0.096	
е	0.650 TYP		0.026 TYP		
e1	1.200	1.400	0.047	0.055	
L	0.525 REF		0.021 REF		
L1	0.260	0.460	0.010	0.018	
θ	0°	8°	0°	8°	



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